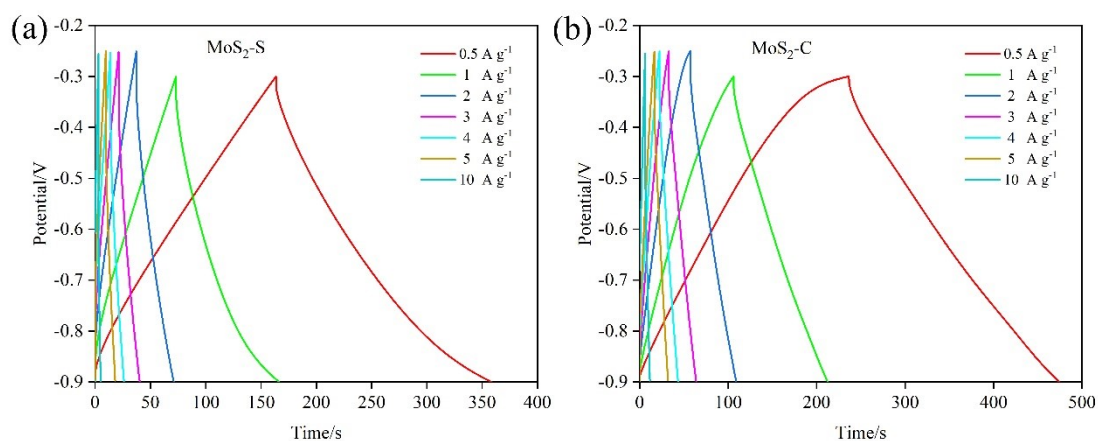


## Designed of hollow structures with different geometries of MoS<sub>2</sub> and comparative study of their capacitive properties

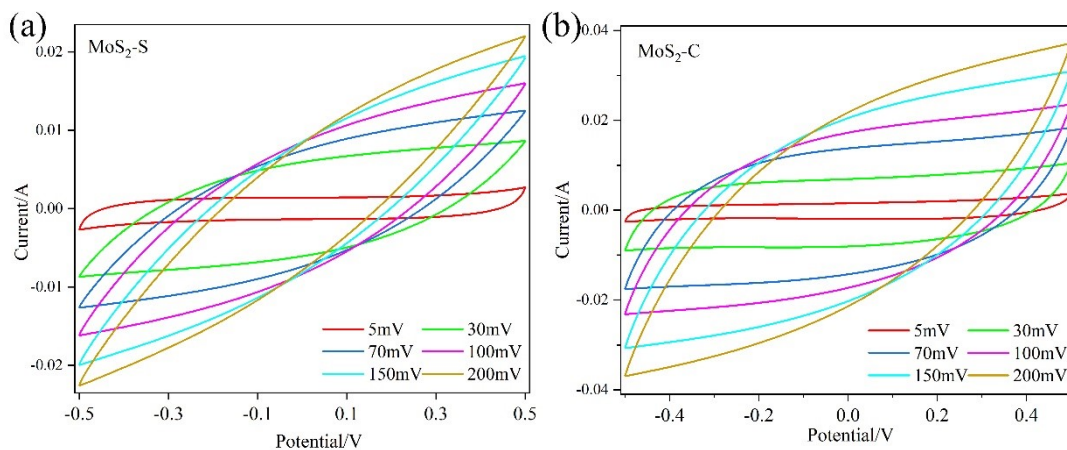
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**Figure S1** The GCD curves of (a) MoS<sub>2</sub>-S, (b) MoS<sub>2</sub>-C.



**Figure S2** The symmetrical device with CV curves of (a) MoS<sub>2</sub>-S, (b) MoS<sub>2</sub>-C.